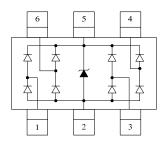


DESCRIPTION

The AZC199-04S a low capacitance of 0.4pF maximum and operates with virtually no insertion loss to 1GHz. This makes the device ideal for protection of high-speed data lines such as USB 2.0, Firewire, DVI, and gigabit interfaces. The low capacitance array configuration allows the user to protect four high-speed data or transmission lines. The low voltage inductance construction minimizes overshoot during high current surges. They may be used to meet the ESD immunity requirements of IEC61000-4-2, Level 4 (±15kV contact discharge).

This device has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and lightning.



FEATURES

- Protects four I/O lines and one Vcc line
- Low capacitance
- Working voltages: 5V
- Low leakage current
- Low capacitance for high-speed interfaces
- No insertion loss to 2.0GHz
- Response Time is < 1 ns

APPLICATIONS

- Digital Visual Interface (DVI)
- USB 1.1/2.0/OTG
- IEEE 1394 Firewire Ports
- Notebooks & Handhelds
- Projection TV & Monitors
- Set-top box
- Flat Panel Displays
- PCI Express



ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Units
P_Pk	Peak Pulse Power (8/20µs)	150	W
I _{PP}	Peak Pulse Current (8/20µs)	5	Α
V _{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±15 ±8	kV
T _{OPT}	Operating Temperature	-55/+150	°C
T _{STG}	Storage Temperature	-55/+150	°C

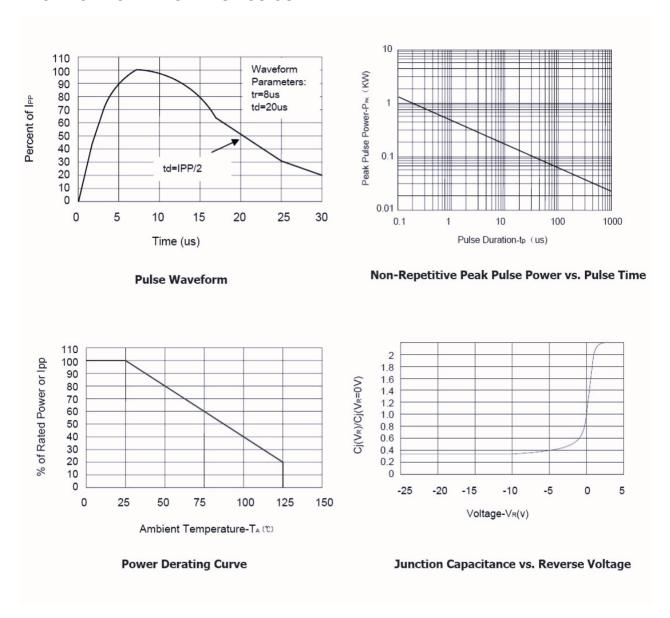
ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
V_{RWM}	Reverse Working Voltage	Any I/O pin to GND			5.0	V
V_{BR}	Reverse Breakdown Voltage	$I_T = 1mA$ Any I/O pin to GND	6.0			V
I _R	Reverse Leakage Current	V _{RWM} = 5V Any I/O pin to GND			1	μΑ
V _F	Diode Forward Voltage	I _F = 15mA			1.2	V
V _{C1}	Clamping Voltage 1	I _{PP} = 1A, t _p = 8/20μs Any I/O pin to GND			15	V
V_{C2}	Clamping Voltage 2	I _{PP} = 5A, t _p = 8/20µs Any I/O pin to GND			28	V
C _{J1}	Junction Capacitance 1	V _R = 0V, f = 1MHz Between I/O pins			0.4	pF
C_{J2}	Junction Capacitance 2	$V_R = 0V$, $f = 1MHz$ Any I/O pin to GND			0.8	pF

Note: I/O pins are pin 1,3,4,6.

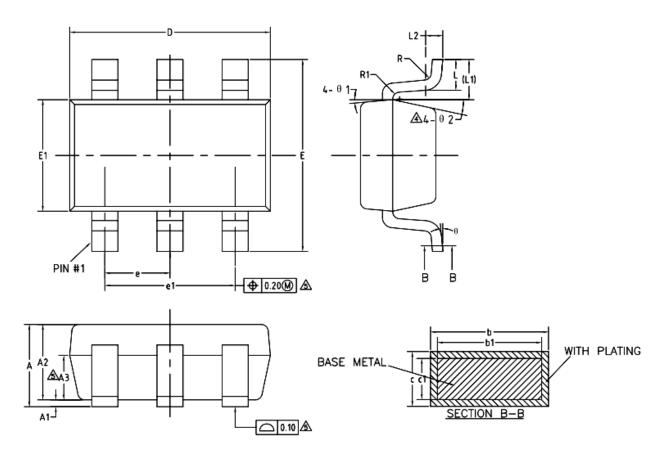


ELECTRICAL CHARACTERISTICS CURVE





SOT23-6



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

	SYMBOL	MIN	NOM	MAX
	Α	-	-	1.25
	A1	0	-	0.15
	A2	1.00	1.10	1.20
	A3	0.60	0.65	0.70
	b	0.36	1	0.50
	b1	0.36	0.38	0.45
	С	0.14	ı	0.20
	c1	0.14	0.15	0.16
	D	2.826	2.926	3.026
	E	2.60	2.80	3.00
	E1	1.526	1.626	1.726
A A	е	0.90	0.95	1.00
▲	e1	1.80	1.90	2.00
	L	0.35	0.45	0.60
	L1	0.59REF		
	L2	0.25BSC		
◬	R	0.10	_	_
◬	R1	0.10	-	0.20
	θ	0,	_	8*
	θ1	3.	5*	7*
Δ	θ 2	6"	-	14"



Marking



Ordering information

Order code	Package	Base qty	Delivery mode
UMW AZC199-04S	SOT23-6	3000	Tape and reel